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14:20 (5-3) Light Irradiation and Applied Voltage History Sensors Using Amorphous In-Ga-Zn-O Thin-Film Transistors Exposed to Ozone Annealing and Fabricated under High Oxygen Pressure
M. Kimura[1], T. Hasegawa[1], T. Matsuda[1], K. Ide[2], K. Nomura[2], T. Kamiya[2], H. Hosono[2], *[1]Ryukoku Univ., Japan , [2]Tokyo Inst. of Technol., Japan* 319

― *Coffee Break* ―

Session 6: Advanced Technologies for TFTs (14: 55 〜 16 : 20)

Chairpersons : G. Fortunato, *IMM-CNR, Italy*
T. Arai, *Sony, Japan*

14:55 (6-1)* Flexible Electronics Based on Oxide Semiconductors (Invited)
L. Petti, N. Münzenrieder, G. A. Salvatore, C. Zysset, T. Kinkeldei, L. Büthe, C. Vogt,
G. Tröster, *Swiss Federal Inst. of Technol., Switzerland* 323

15:20 (6-2)* Homojunction In_2O_3-TFTs Prepared by Anodization Technique
P. Zhang, X. Xiao, L. Wang, Y. Shao, S. Zhang, *Peking Univ., China* 327

15:40 (6-3)* Effect of Aluminum and Indium Composition on the Bias-Illumination-Stress Stability of Solution-Processed Transparent Al-In-Zn-O Thin-Film Transistors
M. -J. Park, J. -Y. Bak, J. -S. Choi, S. -M. Yoon, *Kyung Hee Univ., Korea* 331

16:00 (6-4)* High Performance Raised Source/Drain Thin Film Transistor with Field Plate Design
K. -T. Lin, F. -T. Chien, *Feng Chia Univ., Taiwan* ……………….………..............................335

Closing Remarks (16 : 20 〜 16 : 25)

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